

Sol–gel derived $6\text{CaO}\cdot 6\text{SrO}\cdot 7\text{Al}_2\text{O}_3$ thin films using metal alkoxides

P.M. Chavhan^{a,b,c,*}, Anubha Sharma^b, R.K. Sharma^{a,*}, CheolGi Kim^c, N.K. Kaushik^b

^a Polymeric and Soft Material Section, National Physical Laboratory, Dr. K.S. Krishnan Road, New Delhi 110012, India

^b Department of Chemistry, University of Delhi, Delhi 110007, India

^c Department of Materials Science and Engineering, Chungnam National University, Daejeon-305764, Republic of Korea

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Abstract

The novel $6\text{CaO}\cdot 6\text{SrO}\cdot 7\text{Al}_2\text{O}_3$ (C6S6A7) thin films were deposited onto soda lime glass substrate using calcium, strontium, aluminium isopropoxide and 2-methoxy ethanol as starting materials via sol–gel dip coating technique. The electrical and optical properties of C6S6A7 films were investigated for films sample annealed at 450 °C for 2 h in air and hydrogen (H_2) atmosphere, respectively. X-ray diffraction pattern and Fourier transformed infrared spectroscopy analysis confirms cubic structure to the C6S6A7 material. The optical transmission spectra of C6S6A7 films showed the high transparency in wide visible range of ~ 88 and 80% for air and H_2 annealed samples, respectively. The C6S6A7 films sheet resistance of 528 and 0.65 k Ohm/square has been observed for films annealed in air and H_2 atmosphere at 450 °C, respectively.

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1. Introduction

Alkaline earth metal oxides combined with aluminium oxide have potential use as refractory oxides in the steel industry and binder materials in the cement industry. They are of great interest in materials science because of their use as long-duration photoluminescence and thermo luminescence pigments [1]. In the $\text{CaO}\text{--}\text{Al}_2\text{O}_3$ binary system, $\text{CaO}\cdot\text{Al}_2\text{O}_3$ (CA), $\text{CaO}\cdot 2\text{Al}_2\text{O}_3$ (CA2), $12\text{CaO}\cdot 7\text{Al}_2\text{O}_3$ (C12A7) are the extensively studied oxide which has been exploited during aluminous cement production [2]. There have been numerous reports on C12A7 thin films deposited by pulsed laser deposition (PLD) technique [3–5]. The C12A7 is a promising binary compound with potential uses in electronic and optoelectronic devices [6]. However, it suffers from some drawbacks such as necessity to prepare target material prior to deposition, the chance of particulates deposition and the lack of uniformity over large areas [7,8]. Compared with the better known $\text{CaO}\text{--}\text{Al}_2\text{O}_3$ system, the $\text{SrO}\text{--}\text{Al}_2\text{O}_3$ system [9] has also the existence of SA, SA2 and S12A7 stable double oxides, isostructural with CA,

CA2 and C12A7 (in the cement chemistry notation C = CaO , S = SrO and A = Al_2O_3). S12A7 is a meta-stabilized phase in the $\text{SrO}\text{--}\text{Al}_2\text{O}_3$ system and has the same structure as C12A7 system. S12A7 has larger lattice parameters as compared to C12A7 and, which is converted in to stable electride thin films [10]. The synthesis of bulk S12A7 was first carried out by a sol–gel process [11]. The nanostructured pulsed laser deposited (PLD) C12A7 thin film is a promising binary compound with potential uses in electronic and optoelectronic devices [6] and its nanoporous crystal structure is responsible for the oxygen ion generation, H^- ion emission and electron emission at room temperature [12–15]. However, PLD C12A7 thin films require the preparation of target material prior to deposition and the lack of uniformity over large areas [16]. Moreover in the preparation of multicomponent mixed oxide thin films, the sol–gel process represents an attractive alternative to conventional synthesis methods. Compared to solid state reactions, this mild synthesis method usually results in the formation of mixed oxide of improved homogeneity [17–19].

In present work, we synthesized C6S6A7 thin films using sol–gel dip coating technique wherein six Ca^{2+} ions has been substituted by six Sr^{2+} ions in the cage like C12A7 structure. The C6S6A7 thin films have been characterized by XRD, FT-IR and UV–visible spectroscopy. The optical transparency and sheet resistance of films has been evaluated using UV–visible

* Corresponding authors. Tel.: +91 11 25742610; fax: +91 11 25742612.

E-mail addresses: pandurang.chavhan@gmail.com (P.M. Chavhan), rksharmanpl@rediffmail.com (R.K. Sharma), cgkim@cnu.ac.kr (C.G. Kim).

spectra and four point probe method. Jestin et al. have reported low-loss optical Er^{3+} activated glass-ceramics planar waveguides fabricated by bottom-up approach. The dip coating technique is very useful for fabrication of sol–gel derived integrated optics systems [20]. The sol–gel process is regarded as being a cost-effective and simple technique which can easily lead to the formation of uniform thin films at room temperature offering precise control over the stoichiometry of the deposited film [21].

2. Experimental details

2.1. Materials and solvents

Calcium (Ca) and Strontium (Sr) metal pieces with more than 99% purity were purchased from Sigma–Aldrich Chemie, Germany. Aluminium isopropoxide with more than 99% in purity was purchased from Riedel de Haen, Seelze and 2-methoxy ethanol with more than 99.5% purity was purchased from LOBA Chemie, Pvt. Ltd., Mumbai.

2.2. Preparation of sol

C6S6A7 sol was prepared using stoichiometric amount of Ca-2-ethyl hexonate, Sr-glyconate monomethyl ether and aluminium isopropoxide as precursor materials. Ca-2-ethyl hexonate were prepared by refluxing calcium metal with 2-ethyl hexonic acid using 2-methoxy ethanol as a solvent. Similarly, Sr-glyconate monomethyl ether was prepared by refluxing strontium metal in 2-methoxy ethanol.

As prepared Ca-2-ethyl hexonate and Sr-glyconate monomethyl ether were mixed well by shaking for 10 min to prepare homogenous sol. In this sol an adequate amount of aluminium iso-propoxide was added drop wise with continuous stirring. The solution was diluted to 100 ml by using 2-methoxy ethanol in order to prepare 2% sol [22]. The prepared precursor sol was stirred for 0.5 h and kept 2 h for aging. A schematic representation of sol preparation steps is shown in Fig. 1.

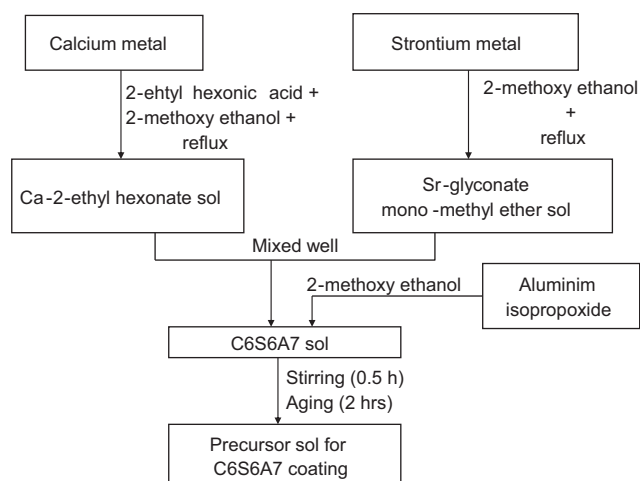


Fig. 1. Schematic representation of precursor sol for C6S6A7 coatings.

2.3. Deposition of C6S6A7 thin films

Soda lime float glass plates (2.5 cm × 7.5 cm) were used for coating of C6S6A7 thin films. Glass plates initially cleaned with distilled water were washed with 10% NaOH (caustic solution) followed by cleaning with distilled water. Again substrate plates were dipped in chromic acid for 5 min to remove associated organic impurities and finally after acid treatment plates were washed with plenty of distilled water and dried in an oven at 120 °C. Prior to coating, glass substrates were again cleaned with acetone and visually checked for dust or any other particles.

Thin films of C6S6A7 were coated onto soda lime float glass substrate using 15 cm/min lifting speed and 2% sol using sol–gel dip coating technique. Desired films thickness has been controlled by multiple coatings. After each coating, they were dried at 100 °C for 10 min. A thickness of about 65 nm of a single layer was obtained. The coating process was repeated 2 and 3 times to synthesize C6S6A7 films of higher thicknesses. Finally all samples were annealed at 450 °C for 2 h in air and H_2 atmosphere, respectively.

2.4. Characterizations

Thickness of the films was measured by using FIL-METRICS-F20 thin film analyzer. X-ray diffraction (XRD) was used for crystal phase identification. XRD measurements were carried out on a Bruker AXS D8 Advance diffractometer using Diffrac^{plus} software. Diffractograms were recorded in grazing incidence geometry using $\text{CuK}\alpha$ radiation. The FT-IR spectra of C6S6A7 films were recorded using Perkin–Elmer Model BX2 spectrophotometer in the wave number range of 400–4000 cm^{-1} . Optical transmission spectra were recorded in the 200–800 nm range using SHIMADZU UV-3101 spectrophotometer at normal incidence. Films sheet resistance was recorded using four probe point measurement method.

3. Results and discussion

3.1. X-ray diffraction analysis

Fig. 2 shows the XRD patterns of C6S6A7 thin films annealed at 450 °C in air atmosphere. The prominent peaks resolved by X-ray diffraction analysis are observed at 20.1, 25.5, 31.8, 36.7, 41.8, 46.9, 54.1, 58.1 diffraction angle which are assigned to 211, 400, 420, 422, 521, 611, 640, 642 lattice planes confirms the cubic phase. However, peaks resolved at 29.9, 44.7 and 50.6 in the diffraction pattern indicate existence of unknown phase in the C6S6A7 material. The appearance of low intensity peaks with unknown phase in the XRD pattern may give deformed cubic structure to the C6S6A7 material. The formation of deformed crystal structure may be because of substitution of six Ca^{2+} ions by six Sr^{2+} ions in the cage like unit cell of C12A7 in the C6S6A7 material. According to Scherrer formula $[D = 0.9\lambda/\beta \cos\theta]$ [23], the particle size of the annealed sample has been calculated to be approximately 6 nm.

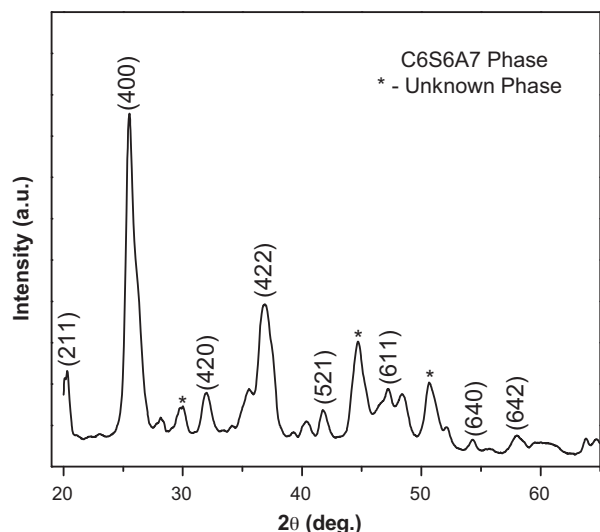


Fig. 2. XRD patterns of C6S6A7 thin films annealed at 450 °C in air atmosphere.

3.2. Fourier transformed infrared spectroscopic analysis

The FT-IR spectra of C6S6A7 thin films annealed at 450 °C in air and H₂ atmosphere is shown in Fig. 3. The most prominent peaks are observed nearly 3545 and 1269 cm⁻¹ due to the presence of absorbed moisture and CO₃⁻ from organometallic precursor or organic solvents traces incorporated during film deposition, respectively [22]. The typical broad strong IR absorption ~815 cm⁻¹ is attributed to the stretching vibrations of Ca–O and Sr–O bonding and stretching vibration peak ~558 cm⁻¹ attributed to Al–O bonding. Moreover, absorption peaks in the 550–850 cm⁻¹ region are attributed to the characteristic absorption corresponding to the Al–O stretching and bending modes in AlO₄ tetrahedral [24,25]. There is a distinguishable and repeatable peak near 3545 cm⁻¹; which assigned to the stretching vibration of O–H on the films surface due moisture present on the films [26–28].

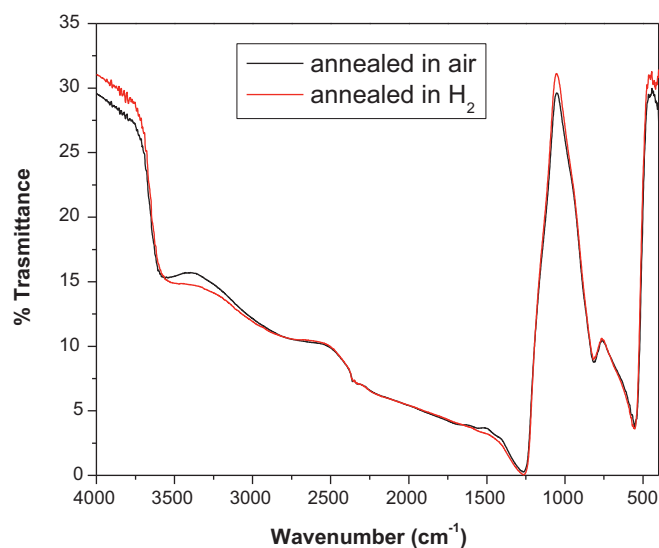


Fig. 3. FT-IR spectrum of C6S6A7 thin films using 2% sol concentrations and annealed at 450 °C.

3.3. Optical properties

Fig. 4a shows the UV–visible transmission pattern of C6S6A7 thin films (129 nm) deposited onto glass substrate and annealed at 450 °C for 2 h in air and H₂ atmosphere. The transmission data of C6S6A7 films annealed in air and H₂ was recorded by dividing transmission of the films to transmission of soda lime glass in all samples. The C6S6A7 films deposited using 2% sol on glass substrate and annealed at in air and H₂ atmosphere showed an average transparency of ~88% and 80% in wide visible range, respectively. The optical transparency is much lower mainly due to electron transitions between the valence and conduction band. In the UV region, the optical transmittance falls sharply, indicating the onset of absorption in this region. The threshold of optical absorption for C6S6A7 films annealed in H₂ atmosphere shifts toward shorter wavelengths, suggesting a broadening of the optical band gap. The observed optical interferences in the transmittance curve indicate a homogenous nature of the film.

In order to calculate the band gap energy (E_{opt}) of the C6S6A7 thin films, we assume the absorption coefficient $\alpha = (1/d)\ln(1/T)$, where T is transmittance and d is the thickness. Fig. 4b shows the graph of $(\alpha h\nu)^2$ Vs. photon energy ($h\nu$) of C6S6A7 films (129 nm) annealed in air and H₂ atmosphere,

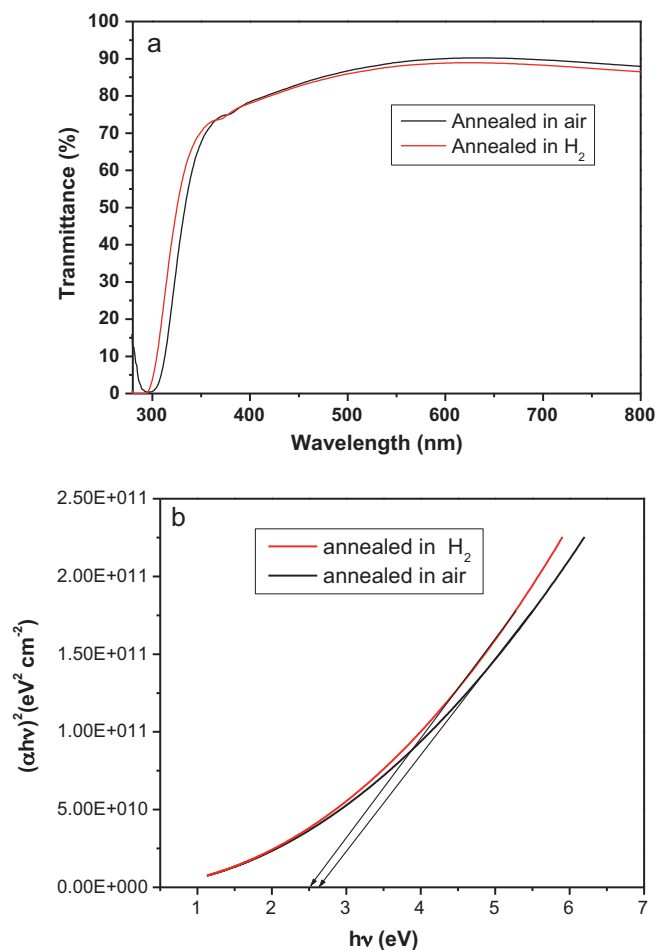


Fig. 4. (a) UV–vis transmission spectra; (b) Plot of $(\alpha h\nu)^2$ Vs. photon energy $h\nu$ of C6S6A7 thin films (129 nm) annealed in air and H₂ at 450 °C for 2 h.

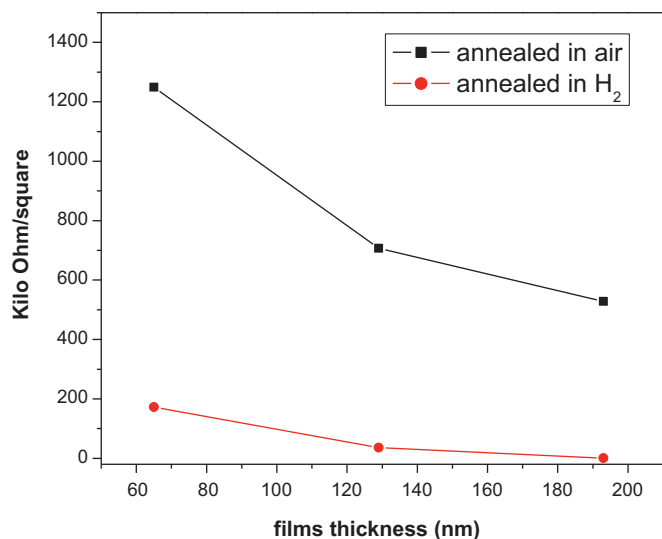


Fig. 5. Variation in sheet resistance values as a function of film thickness for C6S6A7 films annealed at 450 °C in air and H₂ for 2 h.

respectively. The linear dependence of $(\alpha h\nu)^2$ on $h\nu$ at higher photon energies indicate that the C6S6A7 films are essentially direct-transition-type semiconductors. The straight portion of the curve, when extrapolated to zero, gives the optical band gap E_{opt} . The E_{opt} of the C6S6A7 thin films evaluated (Fig. 4b) is nearly 2.51 eV and 2.63 eV for air and H₂ annealed films, respectively.

3.4. Electrical properties

The electrical properties of C6S6A7 thin films derived by sol–gel process have been investigated after thermal treatment in air and H₂ atmosphere. The sheet resistance measurements of C6S6A7 thin films were carried out by taking five readings for each thickness and the mean values are plotted. The error was between $\pm 2\%$. The sheet resistance values have been found to be decreased with increase in the coatings thickness in both air and H₂ annealed C6S6A7 samples. The decrease in sheet resistance with increase coating thickness may be attributed to increase in carrier concentration which gives larger mean free paths and further leads to relatively high carrier mobility. This may be due to fact that at lower thickness films consists of anion trap centers, which may be possibly responsible for high sheet resistance.

The changes in sheet resistance values with changes in coating thickness of C6S6A7 films for samples annealed in air and H₂ atmosphere are shown in Fig. 5. The sheet resistance of C6S6A7 films of 193 nm observed to be 528 and 0.65 k Ohm/square for air and H₂ annealed samples, respectively. The resistance values significantly decreased after annealing in H₂ atmosphere. The significant decreases in sheet resistance values of H₂ annealed films could be attributed to the increase in oxygen vacancies resulting in increase in the carrier concentration and lowering the overall resistivity. This may be ascribed to the larger mean free path which leads to relatively high carrier mobility and thereby lowering the sheet resistance to 0.65 k Ohm/square for C6S6A7 films of nearly

same thickness. It may be mentioned that sheet resistance was measured within a week of sample preparation. However, it has been observed that after one month of deposition the sheet resistance values increased nearly 3% of the values recorded within a week.

4. Conclusions

In the present work, the transparent conducting C6S6A7 thin films have been coated onto soda lime float glass substrate by sol–gel dip coating technique based on hydrolysis, condensation and polycondensation reactions using metal alkoxides. The XRD and FT-IR analyses confirmed that the C6S6A7 films annealed in air/H₂ atmosphere have cubic phase structure. The C6S6A7 films showed an average transparency of $\sim 88\%$ and 80% in wide visible range for air and H₂ annealed samples, respectively. The E_{opt} of the C6S6A7 films has been observed to be enhanced when films has been annealed in H₂ atmosphere. The C6S6A7 films exhibited sheet resistance of 528 and 0.65 k Ohms/square for air and H₂ annealed samples, respectively.

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